

AMENDMENTS TO THE CLAIMS:

Please cancel claims 1 - 13, without prejudice.

This listing of claims will replace all prior versions and listings of claims in the

Application:

Claim 1 (cancelled)

Claim 2 (cancelled)

Claim 3 (cancelled)

Claim 4 (cancelled)

Claim 5 (cancelled)

Claim 6 (cancelled)

Claim 7 (cancelled)

Claim 8 (cancelled)

Claim 9 (cancelled)

Claim 10 (cancelled)

Claim 11 (cancelled)

Claim 12 (cancelled)

Claim 13 (cancelled)

Claim 14 (original): A method of fabricating a semiconductor device comprising:

forming a trench for isolation in said semiconductor substrate; and

forming an insulating film to cover said trench for relaxing an internal stress of said

silicon substrate, wherein said insulating film includes:

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a first portion disposed to be opposed to a bottom of said trench, and
a second portion disposed to be opposed to a side of said trench, and
wherein a first thickness of said first portion is different from a second thickness of said second portion.

Claim 15 (original): The method according to claim 14, wherein said first thickness of said first portion is thinner than said second thickness of said second portion.

Claim 16 (original): The method according to claim 15, further comprising:
forming another insulating film in said trench, wherein said another insulating film exerts a compressive stress on said semiconductor substrate, and said insulating film exerts a tensile stress on said semiconductor substrate.

Claim 17 (original): The method according to claim 15, wherein said insulating film is formed of one selected from a group consisting of silicon oxide and silicon oxinitride.

Claim 18 (original): A method for fabricating a semiconductor device comprising:
forming a trench for isolation in a semiconductor substrate; and
forming an insulating film to cover said trench for relaxing an internal stress of said silicon substrate, wherein said insulating film is opposed to a side of said trench and is not opposed to a bottom of said trench.

Claim 19 (original): The method according to claim 18, further comprising:
forming another insulating film in said trench, wherein said another insulating film exerts a compressive stress on said semiconductor substrate, and said insulating film exerts a tensile stress on said semiconductor substrate.

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Claim 20 (original): The method according to claim 18, wherein said insulating film is formed of one selected from a group consisting of silicon oxide and silicon oxinitride.

Claim 21 (original): A method for fabricating a semiconductor device comprising:
forming a trench for isolation in a semiconductor substrate;
forming a silicon oxide film to cover said trench; and
forming an insulating film on said silicon oxide film, wherein said insulating film exerts a compressive stress on said silicon substrate, and
wherein said insulating film includes:

a first portion disposed to be opposed to a bottom of said trench, and
a second portion disposed to be opposed to a side of said trench, and
wherein a first thickness of said first portion is thinner than a second thickness of said second portion.

Claim 22 (original): The method according to claim 21, wherein said insulating film is formed of one selected from a group consisting of silicon oxide and silicon oxinitride.

Claim 23 (original): A method for fabricating a semiconductor device comprising:
forming a trench for isolation in a semiconductor substrate;
forming a silicon oxide film to cover said trench; and
forming an insulating film on said silicon oxide film, wherein said insulating film is opposed to a side of said trench and is not opposed to a bottom of said trench.

Claim 24 (original): The method according to claim 23, wherein said insulating film is formed of one selected from a group consisting of silicon oxide and silicon oxinitride.

Claim 25 (original): A method for fabricating a semiconductor device comprising:
forming a trench for isolation in a semiconductor substrate;
forming a silicon oxide film to cover said trench; and
forming an insulating film on said silicon oxide film, wherein said insulating film is
formed of one selected from a group consisting of silicon nitride and silicon oxinitride, wherein
said insulating film includes:

 a first portion disposed to be opposed to a bottom of said trench, and
 a second portion disposed to be opposed to a side of said trench, and
wherein a first thickness of said first portion is different from a second thickness of said
second portion.

Claim 26 (original): A method for fabricating a semiconductor device comprising:
forming a trench for isolation in a semiconductor substrate;
forming a silicon oxide film to cover said trench; and
forming an insulating film on said silicon oxide film, wherein said insulating film is
formed of one selected from a group consisting of silicon nitride and silicon oxinitride, wherein
said insulating film is opposed to a side of said trench and is not opposed to a bottom of said
trench.

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